Features

- Ultrafast with Soft Recovery Characteristic (t_{rr} < 30ns)
- +175°C Rated Junction Temperature
- Reverse Voltage Up to 200V
- Avalanche Energy Rated

Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

Description

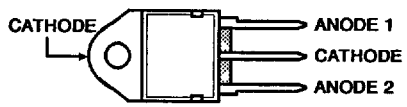
MUR3010PT, MUR3010PT, MUR3020PT and RURD1510, RURD1515, RURD1520 are ultrafast dual diodes (t_{rr} < 30ns) with soft recovery characteristics ($t_a/t_b \approx 1$). They have a low forward voltage drop and are of planar, silicon nitride passivated, ion-implanted, epitaxial construction.

These devices are intended for use as energy steering/ clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits thus reducing power loss in the switching transistor.

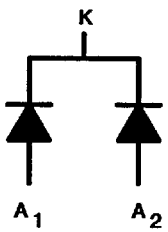
All are supplied in TO-218AC packages.

Package

TO-218AC
TOP VIEW



Symbol



Absolute Maximum Ratings (T_C = +25°C)

		MUR3010PT RURD1510	MUR3010PT RURD1515	MUR3020PT RURD1520
Peak Repetitive Reverse Voltage	V_{RRM}	100V	150V	200V
Working Peak Reverse Voltage	V_{RWM}	100V	150V	200V
DC Blocking Voltage	V_R	100V	150V	200V
Average Rectified Forward Current (Total device forward current at rated V_R and T_C = 150°C)	$I_{F(AV)}$	15A	15A	15A
Peak Forward Repetitive Current (Rated V_R, square wave 20kHZ)	I_{FRM}	30A	30A	30A
Nonrepetitive Peak Surge Current (Surge applied at rated load condition halfwave 1phase 60Hz)	I_{FSM}	200A	200A	200A
Operating and Storage Temperature	T_{STG}, T_J	-55°C to +175°C	-55°C to +175°C	-55°C to +175°C

File Number **2775.2**

Electrical Characteristics (T_C = +25°C) Unless Otherwise Specified.

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SYMBOL	TEST CONDITION	LIMITS									UNITS
		MUR3010PT, RURD1510			MUR3015PT, RURD1515			MUR3020PT, RURD1520			
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V_F	I_F = 15A, T_C = +150°C	-	-	0.85	-	-	0.85	-	-	0.85	V
	I_F = 15A, T_C = +25°C	-	-	1.05	-	-	1.05	-	-	1.05	V
IR @ T_C = +150°C	V_R = 100V	-	-	500	-	-	-	-	-	-	μA
	V_R = 150V	-	-	-	-	-	500	-	-	-	μA
	V_R = 200V	-	-	-	-	-	-	-	-	500	μA
IR @ T_C = +25°C	V_R = 100V	-	-	10	-	-	-	-	-	-	μA
	V_R = 150V	-	-	-	-	-	10	-	-	-	μA
	V_R = 200V	-	-	-	-	-	-	-	-	10	μA
t_{rr}	I_F = 1A	-	-	30	-	-	30	-	-	30	ns
	I_F = 15A	-	-	35	-	-	35	-	-	35	ns
t_a	I_F = 1A	-	18	-	-	18	-	-	18	-	ns
	I_F = 15A	-	20	-	-	20	-	-	20	-	ns
t_b	I_F = 1A	-	9	-	-	9	-	-	9	-	ns
	I_F = 15A	-	10	-	-	10	-	-	10	-	ns
$R_{\Theta jc}$		-	-	1.5	-	-	1.5	-	-	1.5	°C/W
W_{avl}	see Fig. 7&8	-	-	20	-	-	20	-	-	20	mj

Definitions

V_F = Instantaneous forward voltage (pw = 300μs, D = 2%).

I_R = Instantaneous reverse current (pw = 300μs, D = 2%).

t_{rr} = Reverse recovery time at dI_F/dt = 100A/μs (See Figure 2), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current at dI_F/dt = 100A/μs (See Figure 2).

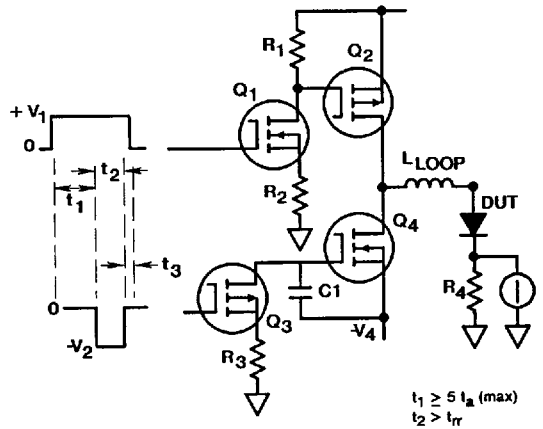
t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM}. (See Figure 2)

$R_{\Theta jc}$ = Thermal resistance junction to case.

W_{avl} = Controlled avalanche energy (See Figures 7 & 8).

pw = pulse width.

D = duty cycle.



V_1 amplitude controls I_F
V_2 amplitude controls di/dt
L_1 = self inductance of R_4

$t_1 \geq 5\ t_a$ (max)
$t_2 > t_{rr}$
$t_3 > 0$
$\frac{L_1}{R_4} \leq \frac{t_a\ (min)}{10}$

FIGURE 1. t_{rr} TEST CIRCUIT

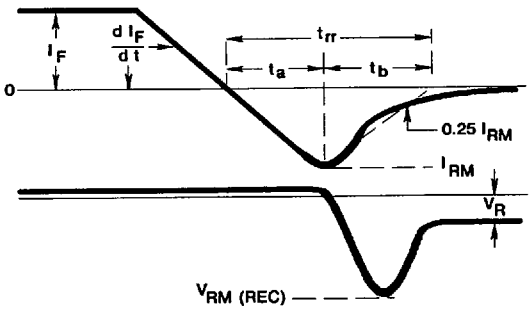


FIGURE 2. DEFINITIONS OF t_{rr}, t_a AND t_b

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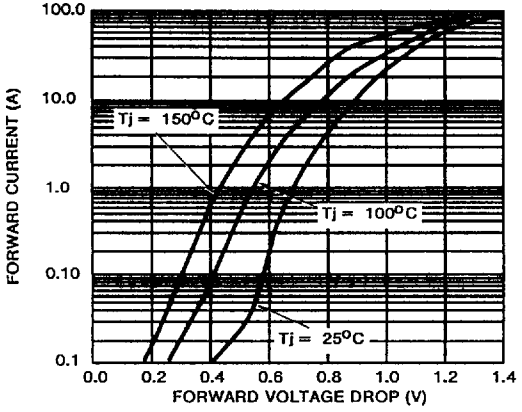

FIGURE 3. FORWARD VOLTAGE vs FORWARD CURRENT CHARACTERISTIC

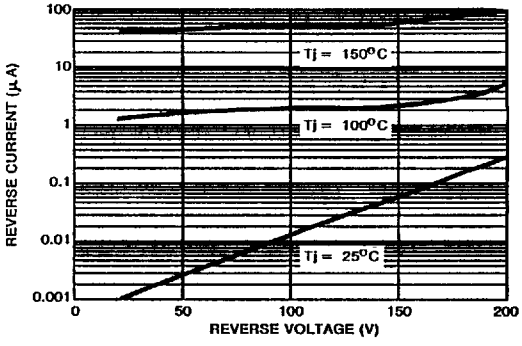

FIGURE 4. REVERSE VOLTAGE vs REVERSE CURRENT CHARACTERISTIC

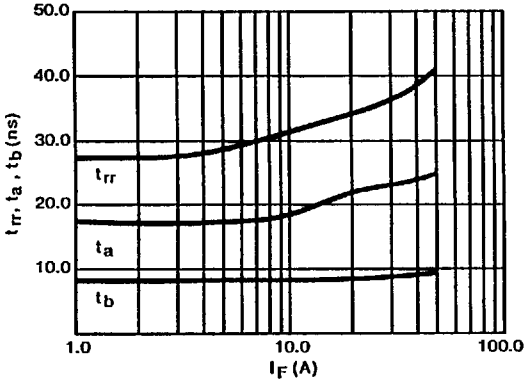

FIGURE 5. TYPICAL t_{rr}, t_a, t_b vs FORWARD CURRENT

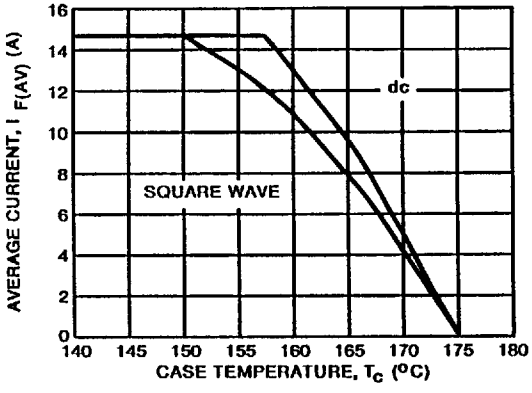

FIGURE 6. TYPICAL CURRENT DERATING CURVE w.r.t. CASE TEMPERATURE

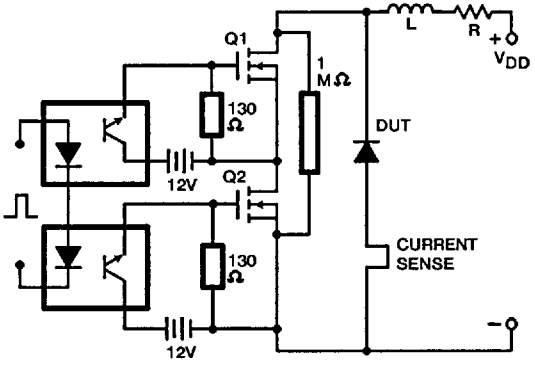

FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

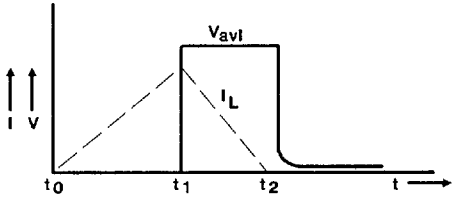

FIGURE 8. CURRENT VOLTAGE WAVEFORM

$I_L$peak = 1A, L = 40mH, R < 0.1Ω, $W_{avl} = (1/2)\ LI^2[V_{avl}/(V_{avl}-V_{dd})]$